

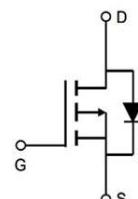
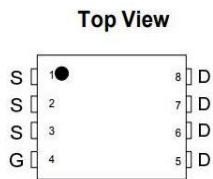
-60V P - Channel MOSFET

Description

-60V /-4A Power MOSFET

Very low on-resistance RDS(on) @ VGS=4.5 V

Pb-free lead plating; RoHS compliant



General Features

V_{DS}	-60	V
R_{DS(on),TYP}@VGS=10V	91.0	mΩ
R_{DS(on),TYP}@VGS=4.5	143.0	mΩ
I_D	-4	A

- High power and current handling capability
- Lead free product is acquired
- Surface mount package

◆ Ordering Information

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
SM4441PRL	SM4441PRG	SOP-8	S	S	S	G	D	D	D	D	Tape Reel
SM4441 X X X (1) Package Type (2) Packing Type (3) Lead Free											
(1) P: SOP-8 (2) R: Tape Reel (3) G: Halogen Free; L: Lead Free											



SM4441

◆ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-4.0	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	-6.4	A
Maximum Power Dissipation	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

a:Fused current that based on wire numbers and diameter

b:Repetitive Rating: Pulse width limited by the maximum junction temperature

c:1-in² 2oz Cu PCB board

◆ Electrical Characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0\text{V}$ $I_D=-250\mu\text{A}$	- 60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-60\text{V}$, $V_{GS}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.5	-2.3	-3	V
Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=-10\text{V}$, $I_D=-6.2\text{A}$	-	91.0	130.0	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5\text{V}$, $I_D=-6.2\text{A}$	-	58	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$	-	930	-	PF
Output Capacitance	C_{oss}		-	85	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $RL=0.75\Omega$, $R_{GEN}=3\Omega$	-	13.5	-	nS
Turn-on Rise Time	t_r		-	10.8	-	nS
Turn-Off Delay Time	$t_{d(\text{off})}$		-	37.8	-	nS
Turn-Off Fall Time	t_f		-	12.15	-	nS
Total Gate Charge	Q_g	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $ID=-4\text{A}$	-	8	-	nC
Gate-Source Charge	Q_{gs}		-	2.24	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$IS=-1\text{A}$, $V_{GS}=0\text{V}$	-	-	-1	V

Note: Pulse Test: Pulse Width $\leq 300\text{us}$, Duty Cycle $\leq 2\%$

d: Guaranteed by design: not subject to production testing

Typical Electrical and Thermal Characteristics

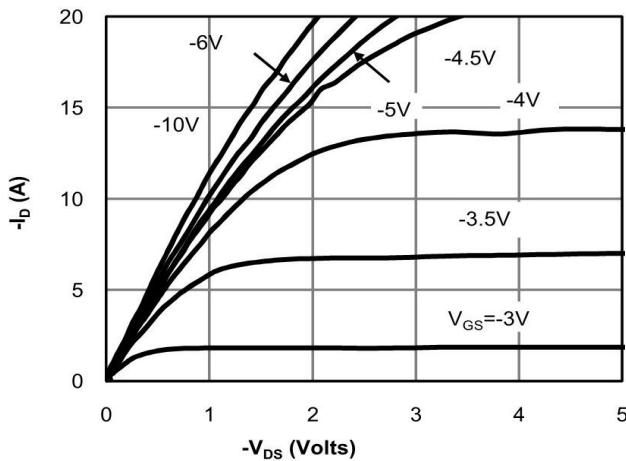


Fig 1: On-Region Characteristics

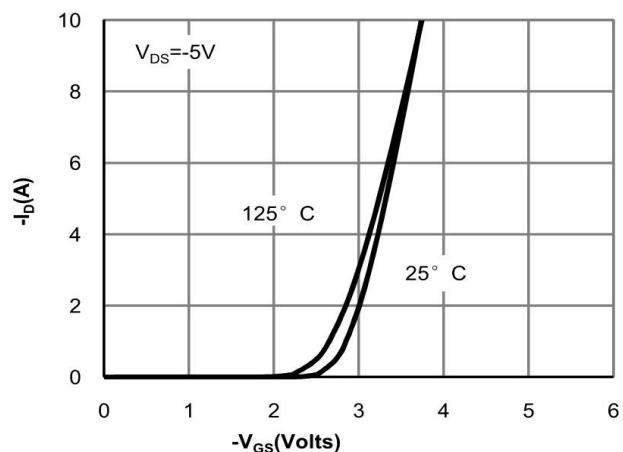


Figure 2: Transfer Characteristics

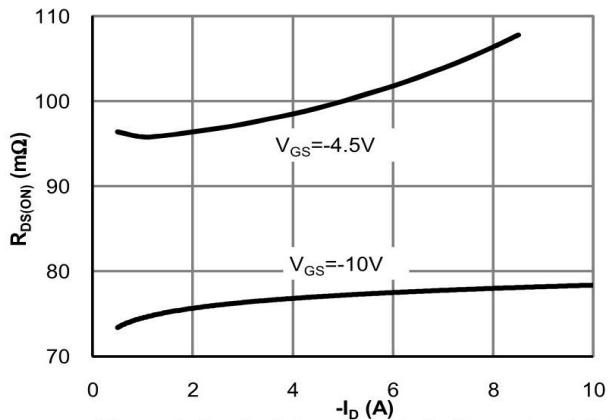


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

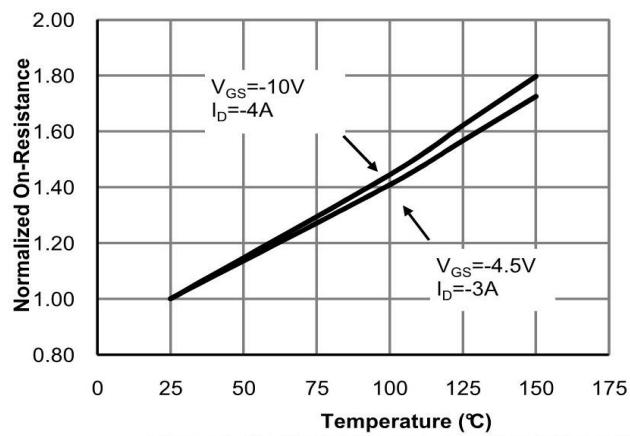


Figure 4: On-Resistance vs. Junction Temperature

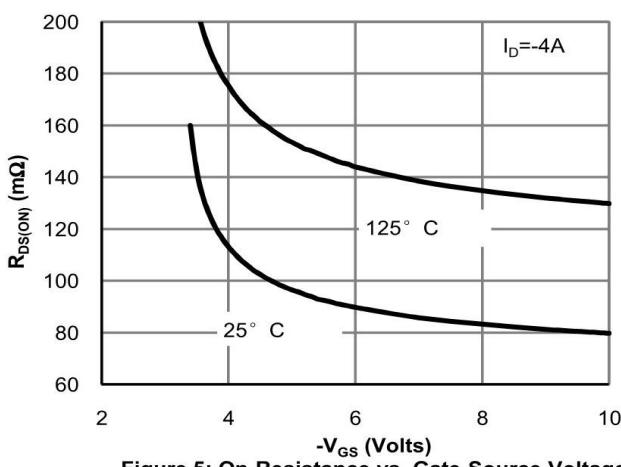


Figure 5: On-Resistance vs. Gate-Source Voltage

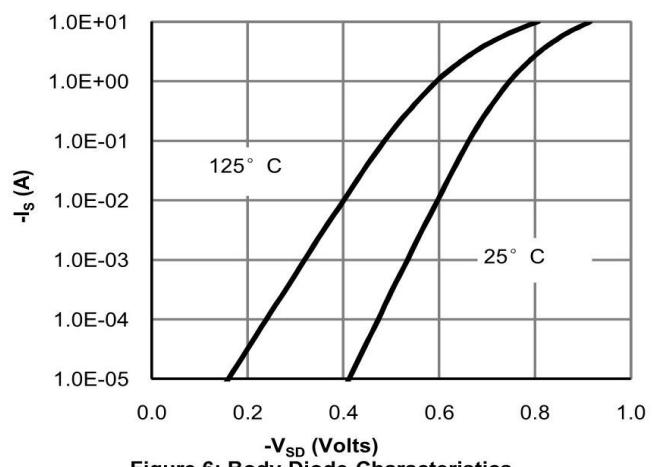


Figure 6: Body-Diode Characteristics

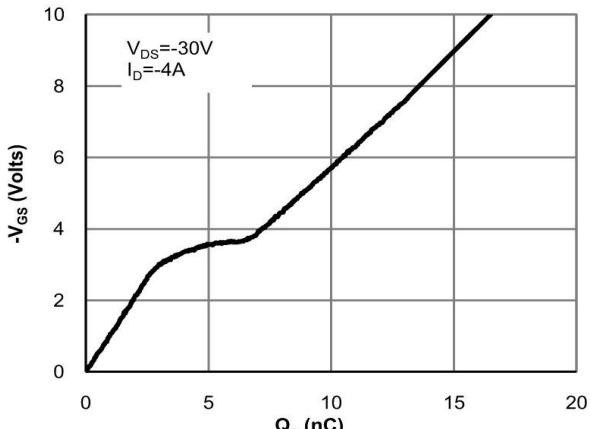


Figure 7: Gate-Charge Characteristics

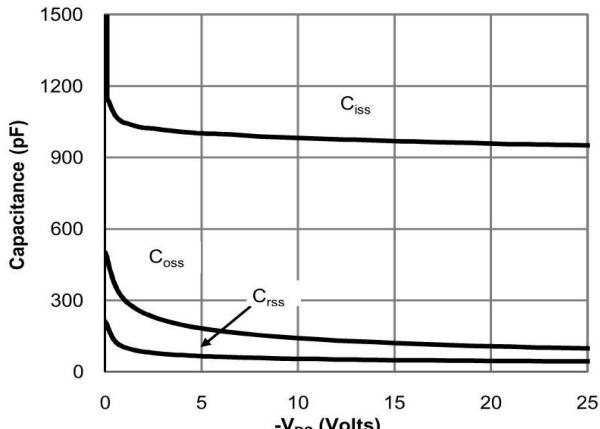


Figure 8: Capacitance Characteristics

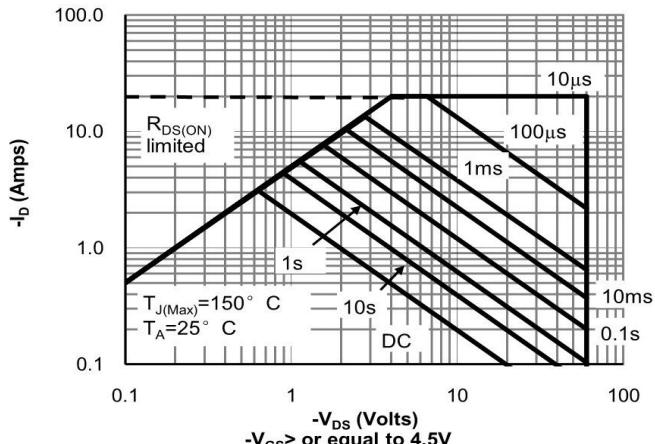


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

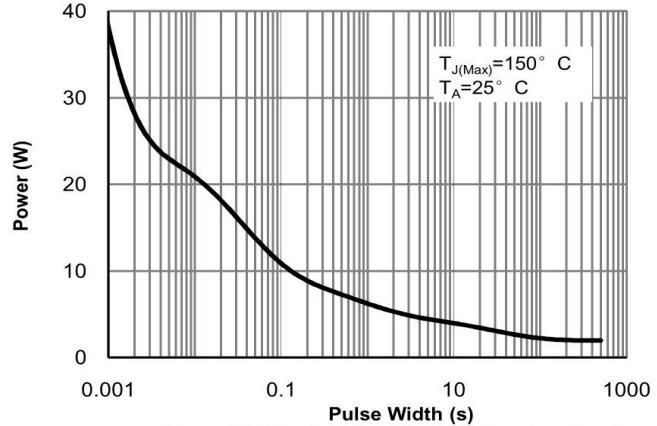


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

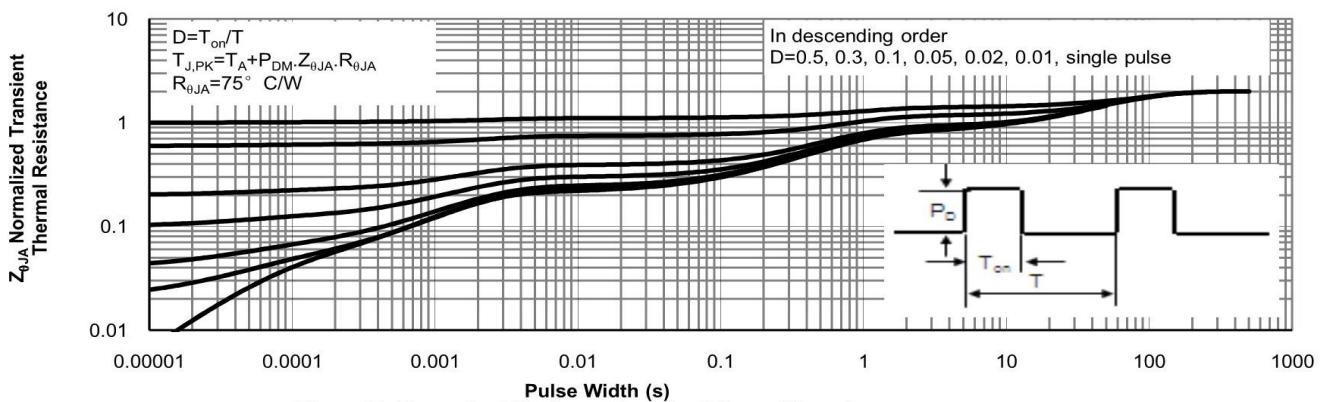
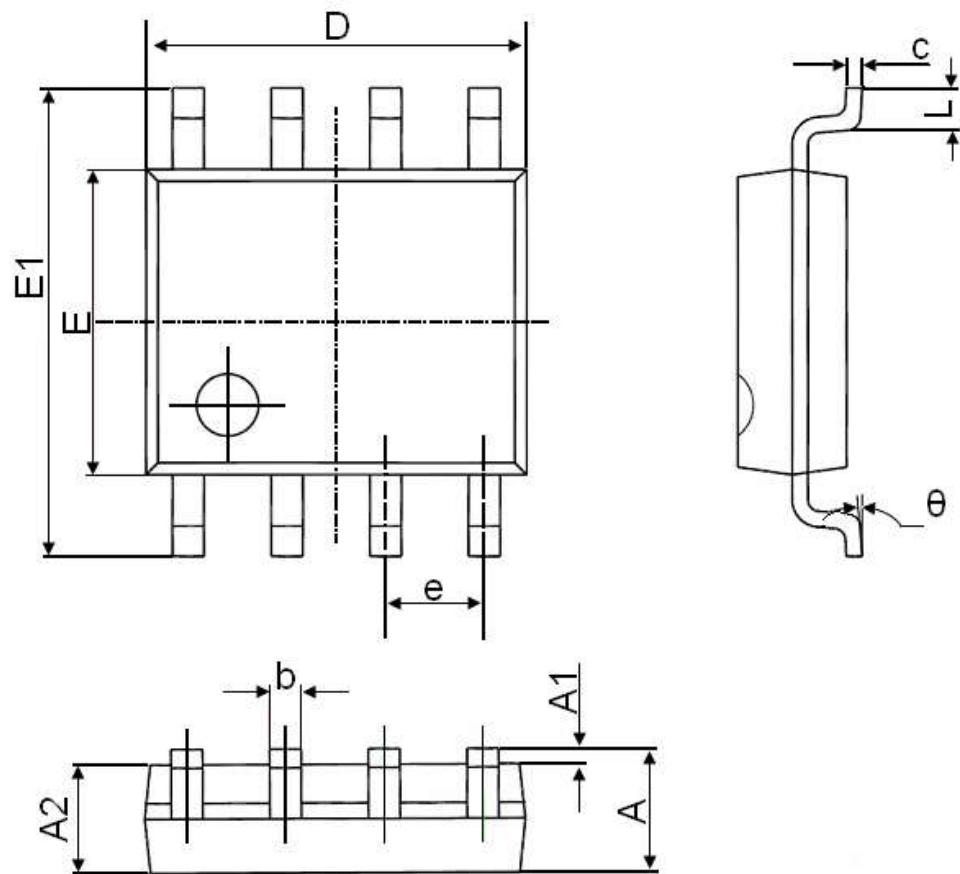


Figure 11: Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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